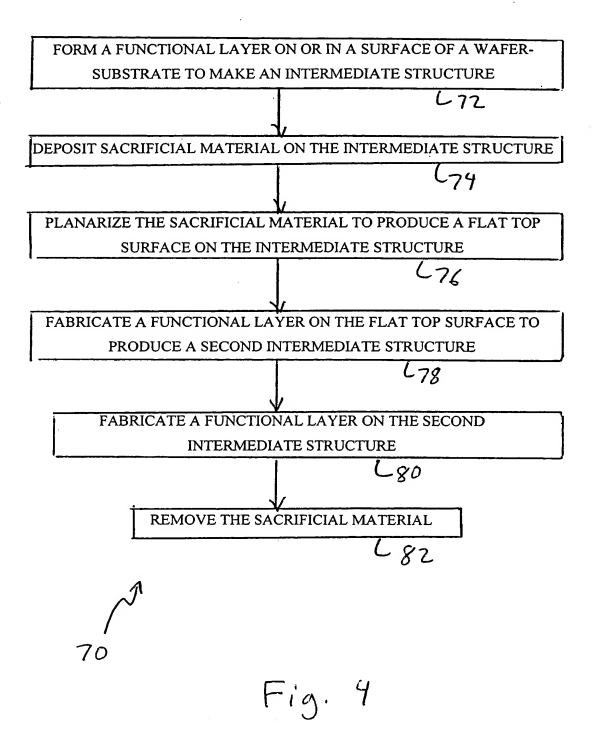


Fig. 2



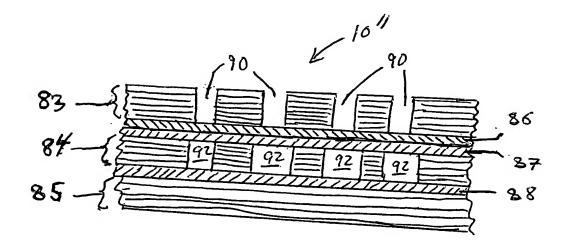
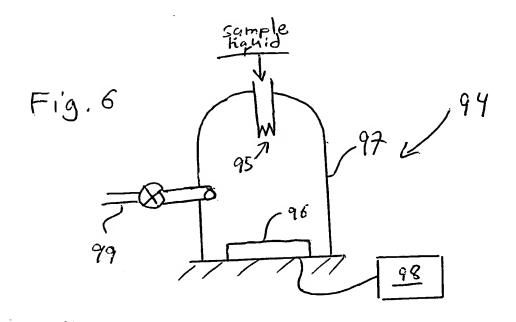
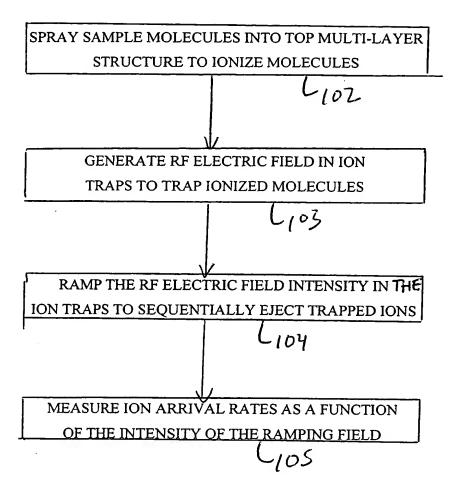


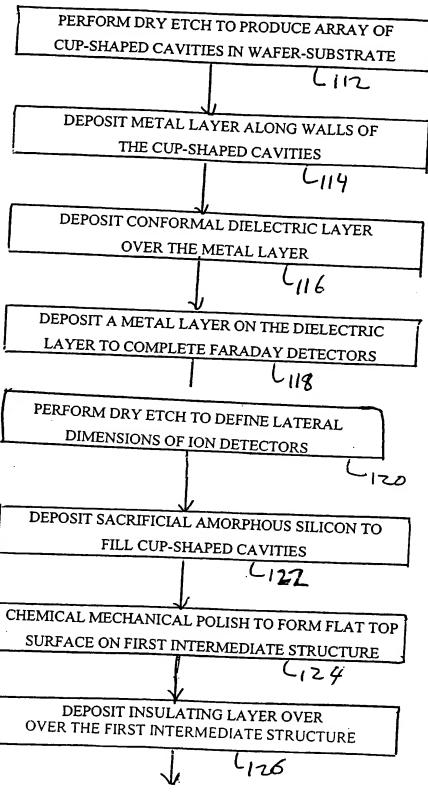
Fig.5

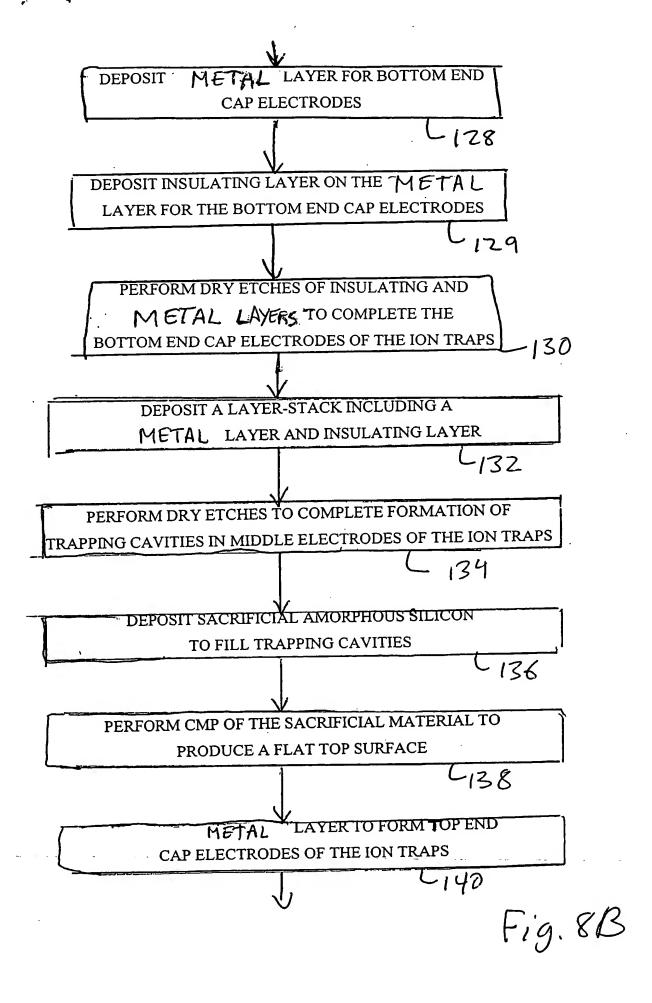




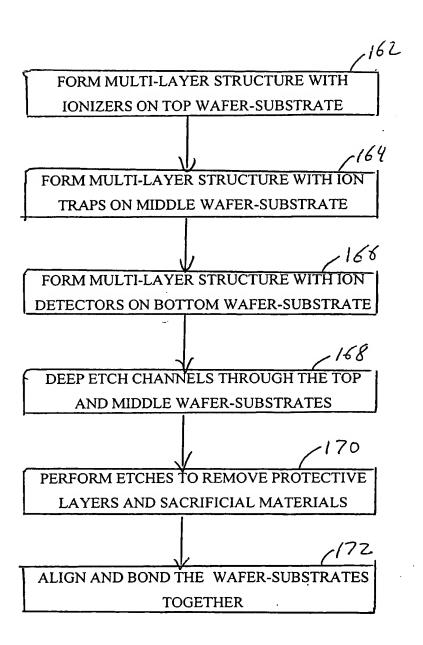
100

. 1-





PERFORM DRY ETCH OF THE DEPOSITED METAL LAYER TO PRODUCE ENTRANCE PORTS FOR THE ION TRAPS L142 DEPOSIT INSULATING LAYER ON THE TOP END CAP ELECTRODES OF THE ION TRAPS 444 DEPOSIT LOWER METAL LAYER OF IONIZERS ON THE INSULATING LAYER -146 PERFORM MASK-CONTROLLED DRY ETCHES TO PRODUCE HOLES THROUGH THE LOWER : METAL LAYER OF IONIZERS AND THE INSULATING LAYER 147 DEPOSIT INSULATING LAYER ON LOWER METAL LAYER FOR THE IONIZERS -148 DEPOSIT UPPER METAL LAYER FOR IONIZERS ON THE INSULATING LAYER 150 PERFORM MASK-CONTROLLED DRY ETCHES TO PRODUCE HOLES THROUGH UPPER METAL LAYER AND INSULATING LAYER OF IONIZERS 152 154 REMOVE SACRIFICIAL AMORPHOUS SILICON tig8c FROM CAVITIES OF THE ION TRAPS AND DETECTORS



160

Fig. 9